





P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) max	I _D T _A = +25°C
-20V	$45m\Omega$ @ $V_{GS} = -4.5V$	-4.3A
	$58m\Omega @ V_{GS} = -2.5V$	-3.8A
	90mΩ @ V _{GS} = -1.8V	-3.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

SOT23



ESD protected Gate



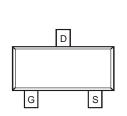
Top View

Features

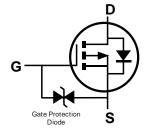
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Top View Internal Schematic



Equivalent Circuit

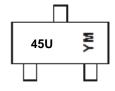
Ordering Information (Note 4)

Part Number Compliance		Case	Packaging
DMP2045U-7	Standard	SOT23	3,000/Tape & Reel
DMP2045U-13	Standard	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



 $45U = Product Type Marking Code YM or <math>\overline{Y}M = Date Code Marking Y or <math>\overline{Y} = Year (ex: F = 2018)$ M = Month (ex: 9 = September)

Date Code Key

Year	2017	20	18	2019	20	020	2021	2	2022	2023		2024
Code	E	F		G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	V			
Gate-Source Voltage	V_{GSS}	±8	V		
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	Ι _D	-4.3 -3.5	А
Maximum Continuous Body Diode Forward Current (Is	-1.2	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-25	A		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	154	°C/W	
Total Power Dissipation (Note 6)		P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	98	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

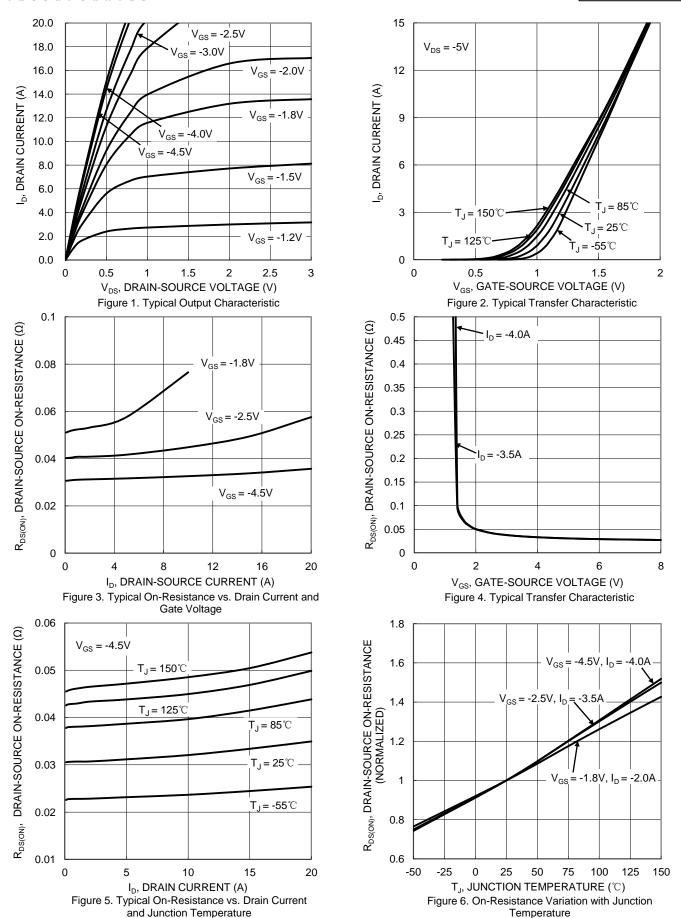
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			•	•	•	
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 8.0 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.3	_	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
		_	32	45		$V_{GS} = -4.5V, I_D = -4.0A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	42	58	mΩ	$V_{GS} = -2.5V, I_D = -3.5A$
		_	54	90		$V_{GS} = -1.8V, I_D = -1.0A$
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V$, $I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	634	_	pF],, ,,,,,
Output Capacitance	Coss	1	81	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	66	_	pF	1 - 1.50011 12
Gate Resistance	R_g	_	20	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge	Q_g	1	6.8	_	nC	
Gate-Source Charge	Q_{gs}	_	0.7	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V$ $I_{D} = -4A$
Gate-Drain Charge	Q_{gd}	_	1.6	_	nC	10 - 40
Turn-On Delay Time	t _{D(ON)}	_	4.2	_	ns	
Turn-On Rise Time	t _R	_	3.4	_	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	23	_	ns	$R_L = 3.3\Omega$, $R_G = 1\Omega$
Turn-Off Fall Time	t _F	_	9.6	_	ns]
Reverse Recovery Time	t _{RR}		1.8	_	ns	I _F = -1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	_	9.4	_	nC	I _F = -1.0A, di/dt = 100A/μs

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.









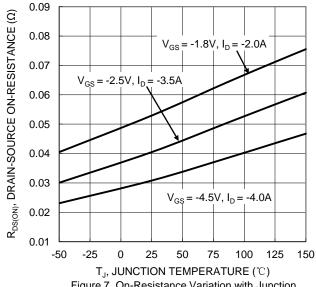


Figure 7. On-Resistance Variation with Junction Temperature

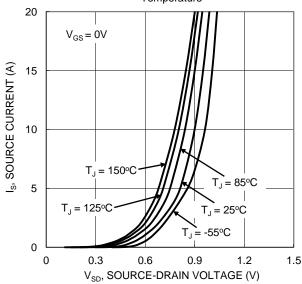
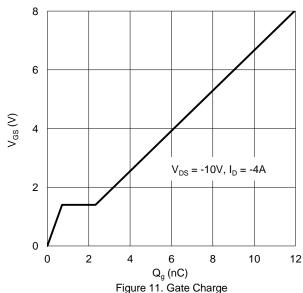
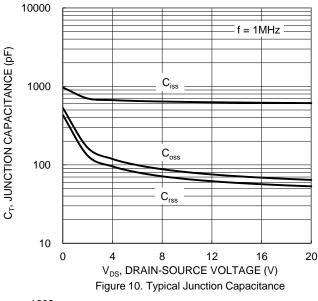


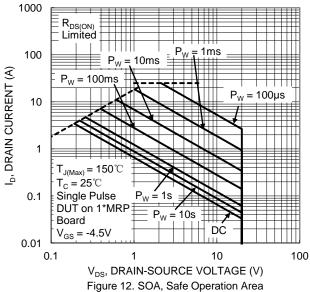
Figure 9. Diode Forward Voltage vs. Current



8.0 $V_{\text{GS}(\text{TH})},$ GATE THRESHOLD VOLTAGE (V) 0.7 0.6 0.5 $I_D = -1mA$ 0.4 0.3 $I_{D} = -250 \mu A$ 0.2 0.1 0 -50 -25 0 25 50 75 100 125 150 T., JUNCTION TEMPERATURE (°C)

Figure 8. Gate Theshold Variation vs. Junction Temperature

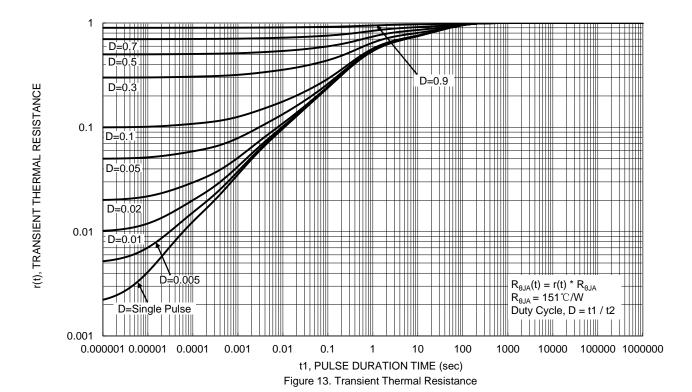




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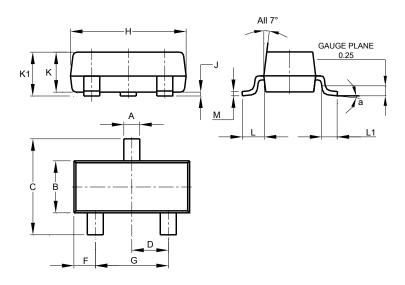




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

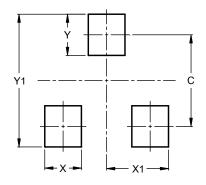


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Υ	0.9
Y1	2.9



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